

PHD16N03LT

N-channel TrenchMOS™ logic level FET

Rev. 01 — 08 March 2004

Product data

1. Product profile

1.1 Description

Logic level N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS™ technology.

1.2 Features

- Logic level threshold
- Fast switching.

1.3 Applications

- DC-to-DC converters
- General purpose switching.

1.4 Quick reference data

- $V_{DS} \leq 30$ V
- $I_D \leq 16$ A
- $P_{tot} \leq 32.6$ W
- $R_{DSon} \leq 67$ m Ω .

2. Pinning information

Table 1: Pinning - SOT428 (D-PAK), simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1	gate (g)	<p>Top view MBK091</p>	<p style="text-align: center;">MBB076</p>
2	drain (d) [1]		
3	source (s)		
mb	mounting base; connected to drain (d)		

SOT428 (D-PAK)

[1] It is not possible to make connection to pin 2 of the SOT428 package.



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3. Ordering information

Table 2: Ordering information

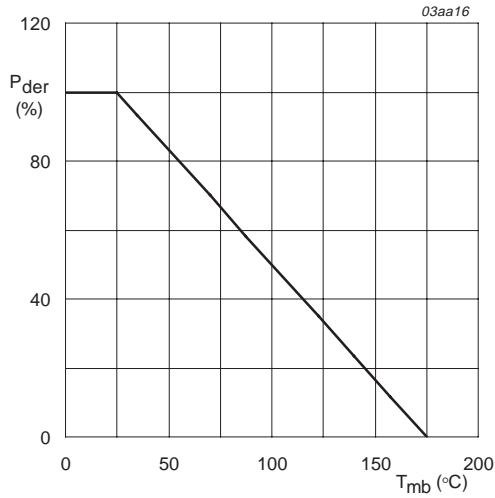
Type number	Package		Version
	Name	Description	
PHD16N03LT	D-PAK	Plastic single-ended surface mounted package; 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 3: Limiting values

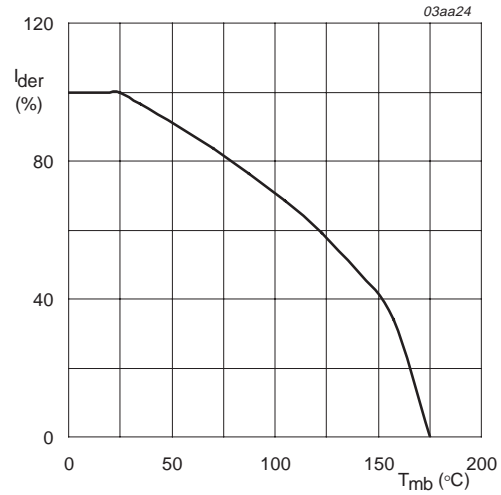
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	30	V
V_{DGR}	drain-gate voltage (DC)	$25\text{ °C} \leq T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage (DC)		-	± 15	V
I_D	drain current (DC)	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; Figure 2 and 3	-	16	A
		$T_{mb} = 100\text{ °C}$; $V_{GS} = 10\text{ V}$; Figure 2	-	11.3	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Figure 3	-	32	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Figure 1	-	32.6	W
T_{stg}	storage temperature		-55	+175	°C
T_j	junction temperature		-55	+175	°C
Source-drain diode					
I_S	source (diode forward) current (DC)	$T_{mb} = 25\text{ °C}$	-	16	A
I_{SM}	peak source (diode forward) current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	32	A



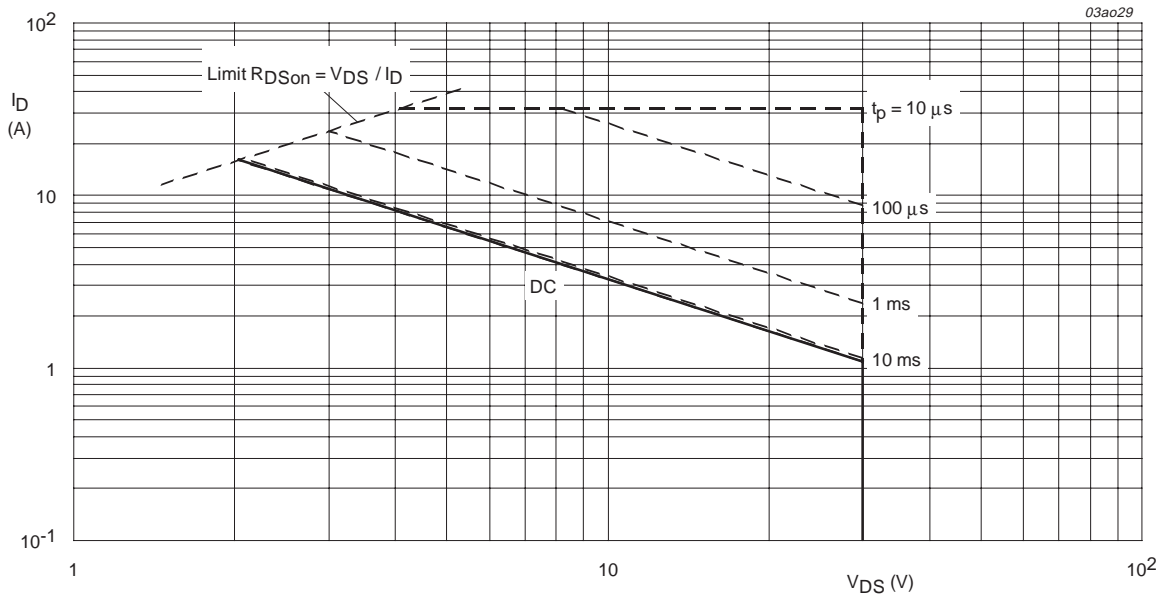
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature.



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of mounting base temperature.



T_{mb} = 25 °C; I_{DM} is single pulse; V_{GS} = 10 V

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	-	-	4.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on a printed-circuit board; vertical in still air; SOT428 minimum footprint	-	75	-	K/W
		mounted on a printed-circuit board; vertical in still air; SOT404 minimum footprint	-	50	-	K/W

5.1 Transient thermal impedance

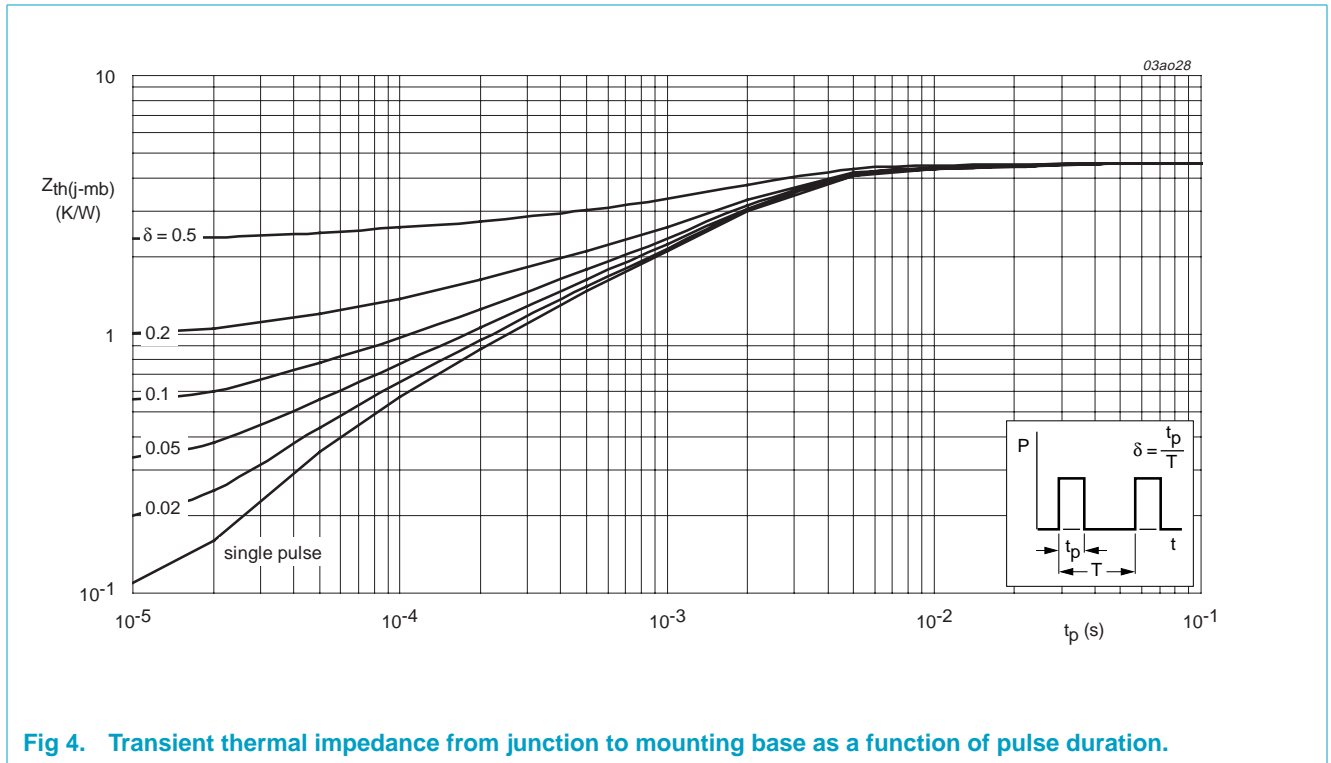


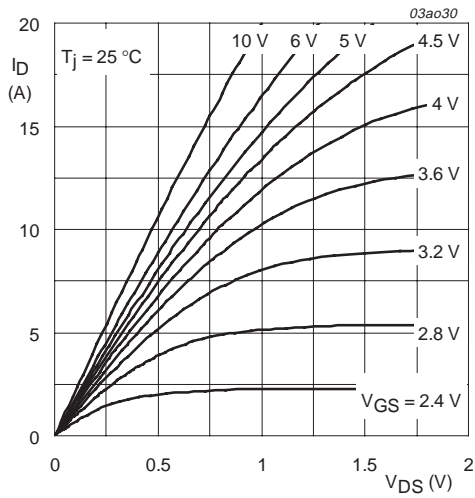
Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration.

6. Characteristics

Table 5: Characteristics

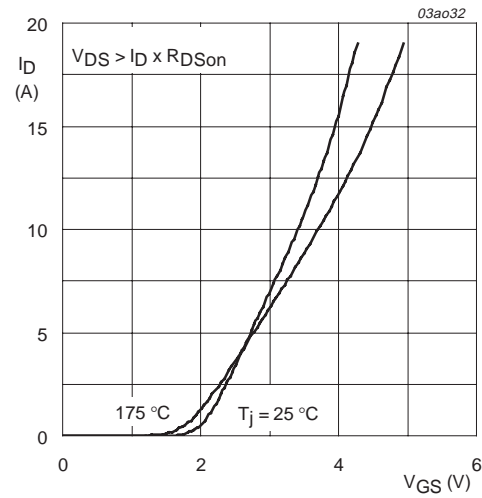
$T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu\text{A}; V_{GS} = 0\ \text{V}$				
		$T_j = 25\text{ °C}$	30	-	-	V
		$T_j = -55\text{ °C}$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\ \text{mA}; V_{DS} = V_{GS};$ Figure 9				
		$T_j = 25\text{ °C}$	1	1.5	2	V
		$T_j = 175\text{ °C}$	0.5	-	-	V
		$T_j = -55\text{ °C}$	-	-	2.2	V
I_{DSS}	drain-source leakage current	$V_{DS} = 30\ \text{V}; V_{GS} = 0\ \text{V}$				
		$T_j = 25\text{ °C}$	-	-	10	μA
		$T_j = 175\text{ °C}$	-	-	500	μA
I_{GSS}	gate-source leakage current	$V_{GS} = \pm 20\ \text{V}; V_{DS} = 0\ \text{V}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\ \text{V}; I_D = 16\ \text{A};$ Figure 7 and 8				
		$T_j = 25\text{ °C}$	-	50	67	m Ω
		$T_j = 175\text{ °C}$	-	95	127	m Ω
		$V_{GS} = 4.5\ \text{V}; I_D = 13\ \text{A};$ Figure 7	-	76	100	m Ω
Dynamic characteristics						
$Q_{g(tot)}$	total gate charge	$I_D = 15\ \text{A}; V_{DS} = 15\ \text{V}; V_{GS} = 10\ \text{V};$ Figure 13	-	8.5	-	nC
Q_{gs}	gate-source charge		-	1.8	-	nC
Q_{gd}	gate-drain (Miller) charge		-	2	-	nC
C_{iss}	input capacitance	$V_{GS} = 0\ \text{V}; V_{DS} = 30\ \text{V}; f = 1\ \text{MHz};$ Figure 11	-	210	-	pF
C_{oss}	output capacitance		-	85	-	pF
C_{rss}	reverse transfer capacitance		-	60	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DD} = 15\ \text{V}; R_L = 1\ \Omega;$ $V_{GS} = 10\ \text{V}; R_G = 5.6\ \Omega$	-	8	-	ns
t_r	rise time		-	6	-	ns
$t_{d(off)}$	turn-off delay time		-	15.5	-	ns
t_f	fall time		-	5	-	ns
Source-drain diode						
V_{SD}	source-drain (diode forward) voltage	$I_S = 10\ \text{A}; V_{GS} = 0\ \text{V};$ Figure 12	-	0.98	1.2	V



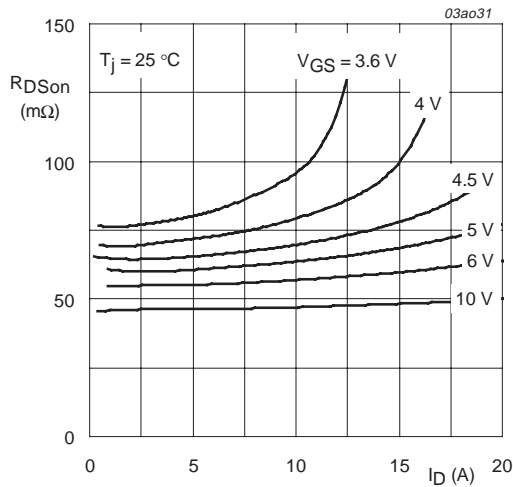
$T_j = 25\text{ }^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



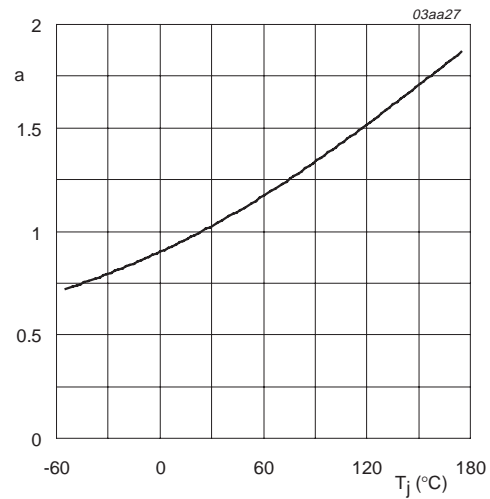
$T_j = 25\text{ }^\circ\text{C}$ and $175\text{ }^\circ\text{C}$; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



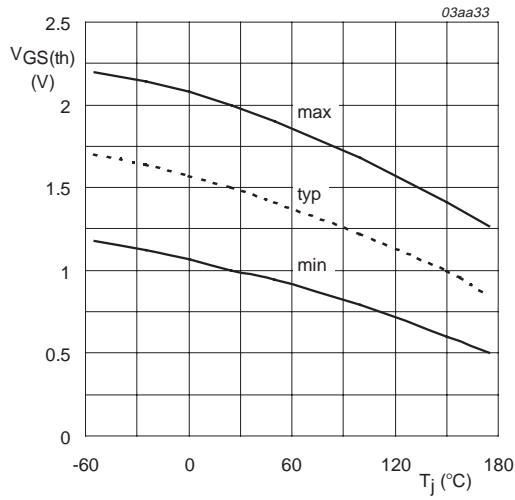
$T_j = 25\text{ }^\circ\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



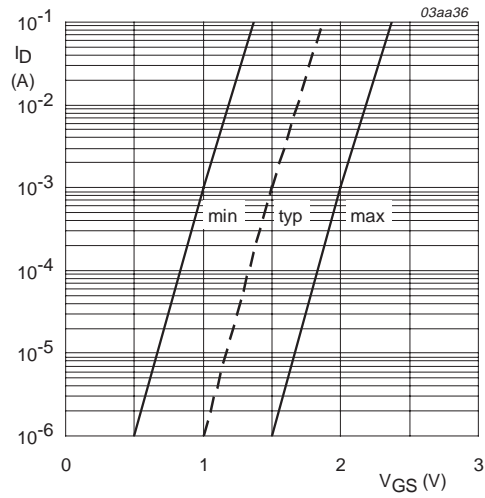
$$a = \frac{R_{DSon}}{R_{DSon}(25\text{ }^\circ\text{C})}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



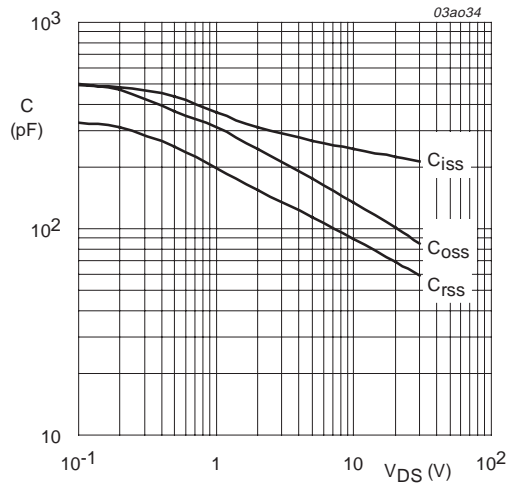
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



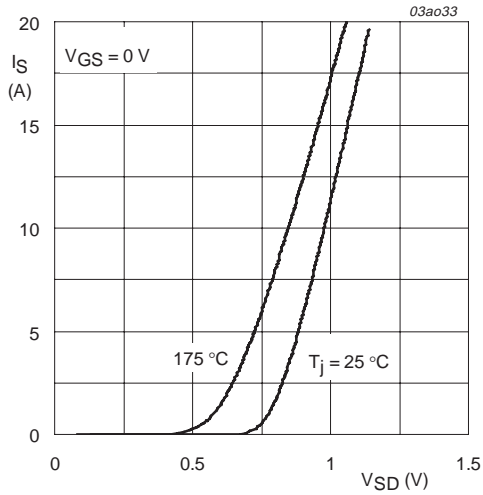
$T_j = 25 \text{ °C}; V_{DS} = 5 \text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



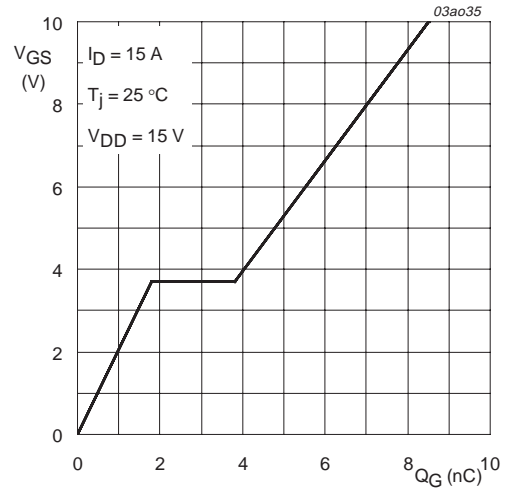
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$T_j = 25\text{ }^\circ\text{C}$ and $175\text{ }^\circ\text{C}$; $V_{GS} = 0\text{ V}$

Fig 12. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.



$I_D = 15\text{ A}$; $V_{DD} = 15\text{ V}$

Fig 13. Gate-source voltage as a function of gate charge; typical values.

7. Package outline

Plastic single-ended surface mounted package (Philips version of D-PAK); 3 leads (one lead cropped)

SOT428

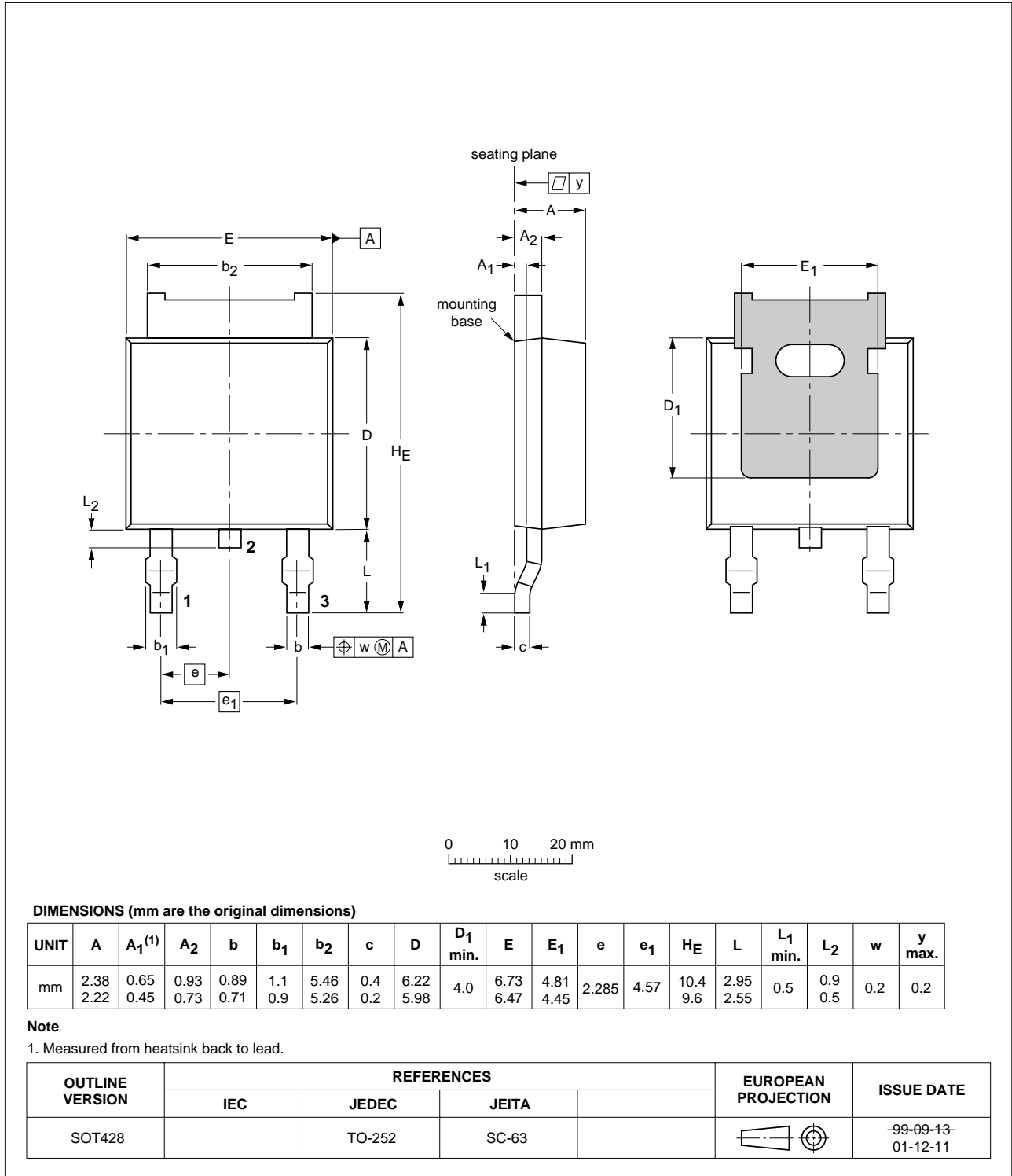


Fig 14. SOT428 (D-PAK).

8. Revision history

Table 6: Revision history

Rev	Date	CPCN	Description
01	20040308	-	Product data (9397 750 12382).

9. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2][3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Contents

1	Product profile	1
1.1	Description	1
1.2	Features	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	1
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	4
5.1	Transient thermal impedance	4
6	Characteristics	5
7	Package outline	9
8	Revision history	10
9	Data sheet status	11
10	Definitions	11
11	Disclaimers	11
12	Trademarks	11

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Date of release: 08 March 2004

Document order number: 9397 750 12382



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